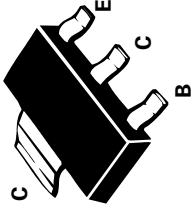


**SOT223 PNP SILICON PLANAR  
MEDIUM POWER TRANSISTOR**

ISSUE 2 – MARCH 1995

**FZT549**

PARTMARKING DETAIL – FZT549



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CB0}$	-35	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-2	A
Continuous Collector Current	$I_C$	-1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_J; T_{stg}$	-55 to +150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$ ).**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-35			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30			V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$		-0.1 -10		$\mu A$ $\mu A$	$V_{CB} = -30V$ $V_{CB} = -30V, T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$		-0.1		$\mu A$	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.50 -0.75		V	$I_C = -1A, I_B = -100mA^*$ $I_C = -2A, I_B = -200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.25		V	$I_C = -1A, I_B = -100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.0		V	$I_C = -1A, V_{CE} = -2V^*$
Static Forward Current	$I_{FE}$	70 100 80 30		300		$I_C = -50mA, V_{CE} = -2V$ $I_C = -500mA, V_{CE} = -2V^*$ $I_C = -1A, V_{CE} = -2V^*$ $I_C = -2A, V_{CE} = -2V^*$
Transition Frequency	$f_T$	100			MHz	$I_C = -100mA, V_{CE} = -5V,$ $f = 100MHz$
Output Capacitance	$C_{obo}$			10	pF	$V_{CB} = -10V, f = 1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$   
For typical characteristics graphs see FM1M549 datasheet.